

#19/D

Attorney Docket No. 03692.P007XD

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

RUMENNIK, et al.

Serial No. 09/574,563

Filing Date: May 17, 2000

For: HIGH-VOLTAGE TRANSISTOR WITH
MULTI-LAYER CONDUCTION REGION

Examiner: Hu, S.

Art Unit: 2811

9/25/02
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Amendment and Response

Hon. Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

This amendment and response is being submitted together with a Request for Continued Examination (RCE) following the Final Office Action mailed May 31, 2002, Applicants respectfully request the following amendments be entered and the

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following remarks be considered:

01 FC:103 198.00 CH
02 FC:102 84.00 CH

In The Claims:

1. (Unchanged) A high voltage field-effect transistor (HVFET) comprising:
a substrate of a first conductivity type;
a first region of a second conductivity type disposed within the substrate;
a source diffusion region of the second conductivity type disposed in the substrate spaced-apart from the first region, a channel region being formed in the substrate between the source diffusion region and the first region;